

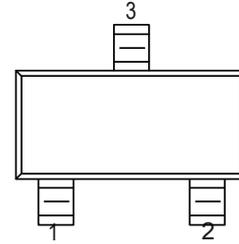
## SOT-23-3 Plastic-Encapsulate MOSFETS

### Features

- -20V,-3.0A,  $R_{DS(ON)} = 70m\Omega @ V_{GS} = -4.5V$
- Improved dv/dt capability
- Fast switching
- Green Device Available

SOT-23-3L

RoHS  
COMPLIANT

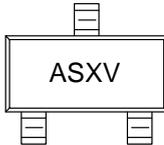


1. GATE
2. SOURCE
3. DRAIN

### Applications

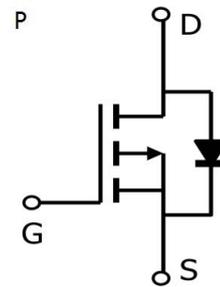
- Notebook
- Load Switch
- Battery Protection
- Hand-Held Instruments

### Marking



ASXV = Device code

### Equivalent Circuit



### Absolute Maximum Ratings $T_c=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D$	Drain Current – Continuous ( $T_c=25^\circ C$ )	-3.0	A
	Drain Current – Continuous ( $T_c=100^\circ C$ )	-2.1	A
$I_{DM}$	Drain Current – Pulsed <sup>1</sup>	-13.2	A
$P_D$	Power Dissipation ( $T_c=25^\circ C$ )	1.56	W
	Power Dissipation – Derate above $25^\circ C$	0.012	W/ $^\circ C$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	80	$^\circ C/W$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**
**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-20	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA	---	-0.01	---	V/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	-1	uA
		V <sub>DS</sub> =-16V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	---	---	-10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V	---	---	±10	uA

**On Characteristics**

R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A	---	70	85	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-2A	---	95	120	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-0.3	-0.6	-1.0	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	3	---	mV/°C
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-10V, I <sub>S</sub> =-1A	---	2.2	---	S

**Dynamic and switching Characteristics**

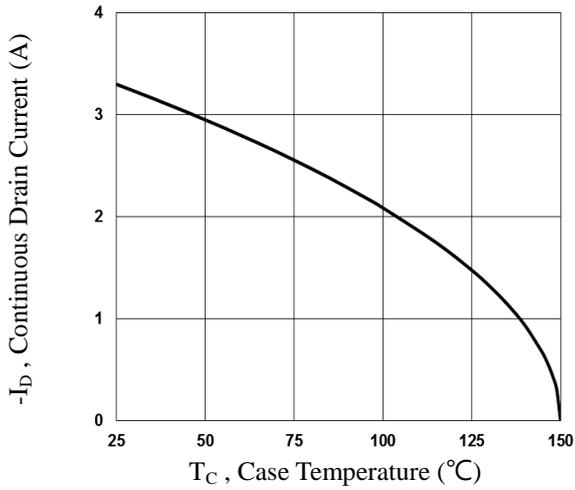
Q <sub>g</sub>	Total Gate Charge <sup>2,3</sup>	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A	---	4.8	---	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>2,3</sup>		---	0.5	---	
Q <sub>gd</sub>	Gate-Drain Charge <sup>2,3</sup>		---	1.9	---	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>2,3</sup>	V <sub>DD</sub> =-10V, V <sub>GS</sub> =-4.5V, R <sub>G</sub> =25Ω I <sub>D</sub> =-1A	---	3.5	---	nS
T <sub>r</sub>	Rise Time <sup>2,3</sup>		---	12.6	---	
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>2,3</sup>		---	32.6	---	
T <sub>f</sub>	Fall Time <sup>2,3</sup>		---	8.4	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, F=1MHz	---	350	---	pF
C <sub>oss</sub>	Output Capacitance		---	65	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	50	---	

**Drain-Source Diode Characteristics and Maximum Ratings**

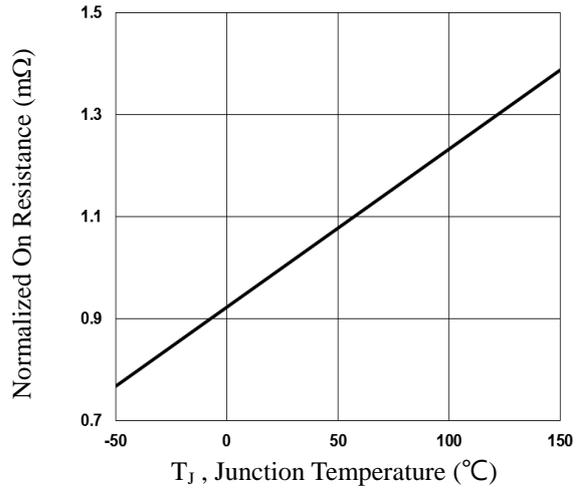
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	-3.0	A
I <sub>SM</sub>	Pulsed Source Current		---	---	-13.2	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A, T <sub>J</sub> =25°C	---	---	-1.2	V

Note :

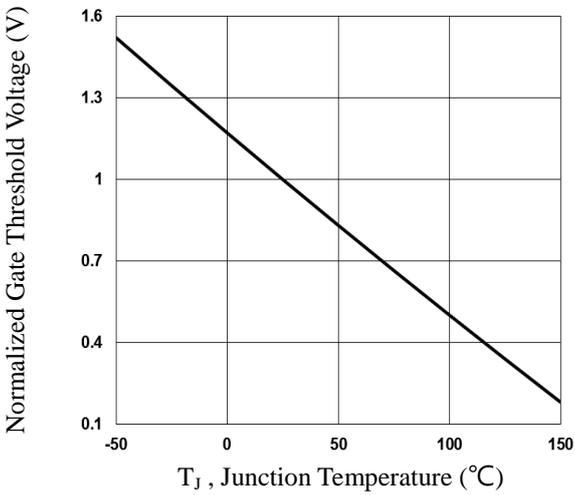
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
3. Essentially independent of operating temperature.



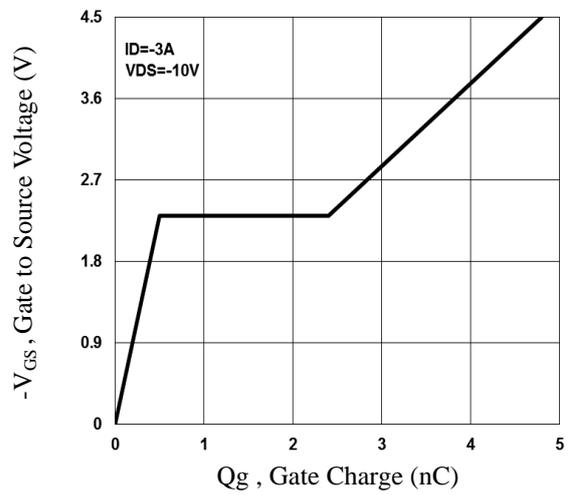
**Fig.1 Continuous Drain Current vs.  $T_c$**



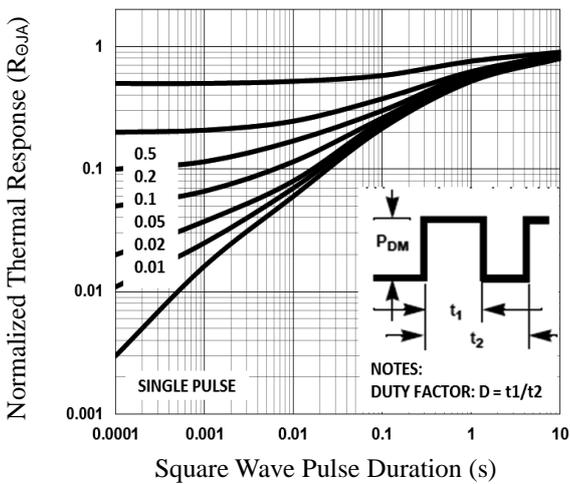
**Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_j$**



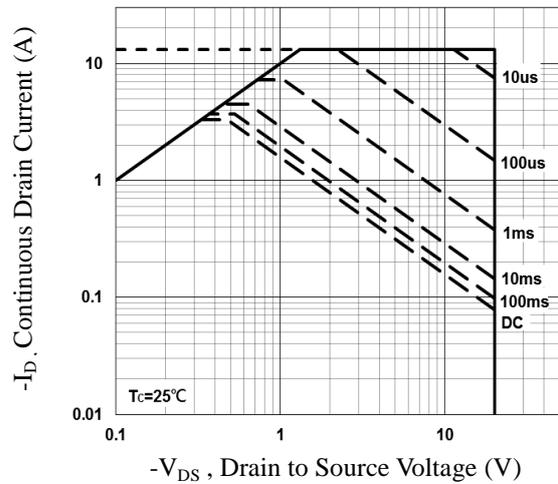
**Fig.3 Normalized  $V_{th}$  vs.  $T_j$**



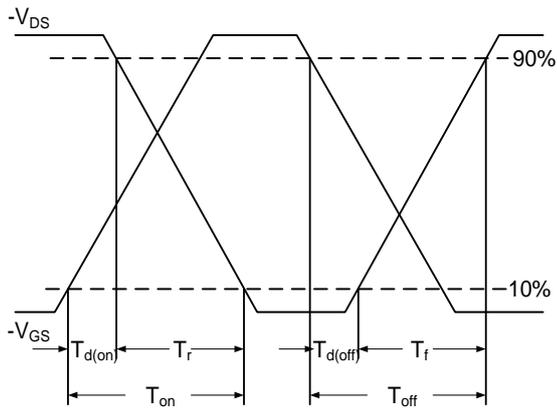
**Fig.4 Gate Charge Waveform**



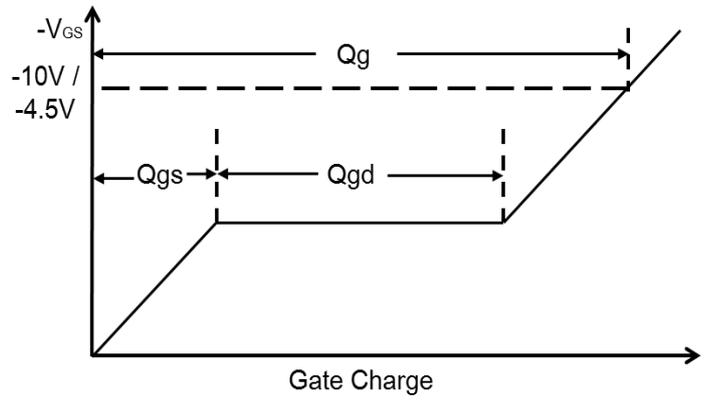
**Fig.5 Normalized Transient Response**



**Fig.6 Maximum Safe Operation Area**

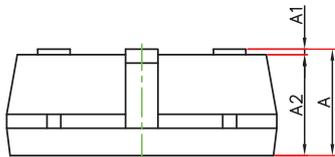
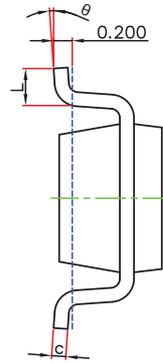
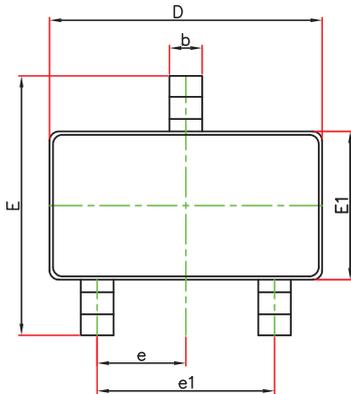


**Fig.7 Switching Time Waveform**



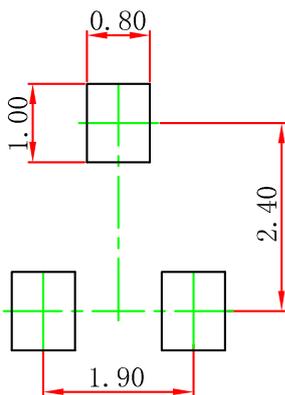
**Fig.8 Gate Charge Waveform**

SOT-23-3L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
K	0°	8°	0°	8°

SOT-23-3L Suggested Pad Layout



- Note:
1. Controlling dimension: in/millimeters.
  2. General tolerance: ±0.05mm.
  3. The pad layout is for reference purposes only.